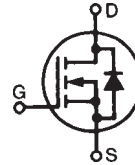


# HiPerFET™ Power MOSFETs Q-Class

**IXFN 44N50Q**  
**IXFN 48N50Q**

$V_{DSS}$	$I_{D25}$	$R_{DS(on)}$
500 V	44 A	120 mΩ
500 V	48 A	100 mΩ

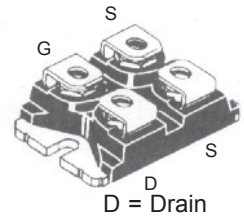
N-Channel Enhancement Mode  
Avalanche Rated, Low  $Q_g$ , High  $dv/dt$



$t_{rr} \leq 250$  ns

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	500	V
$V_{DGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ ; $R_{GS} = 1$ MΩ	500	V
$V_{GS}$	Continuous	±20	V
$V_{GSM}$	Transient	±30	V
$I_{D25}$	$T_C = 25^\circ\text{C}$	44N50	44 A
		48N50	48 A
$I_{DM}$	$T_C = 25^\circ\text{C}$ , pulse width limited by $T_{JM}$	44N50	176 A
		48N50	192 A
$I_{AR}$	$T_C = 25^\circ\text{C}$	48	A
$E_{AR}$	$T_C = 25^\circ\text{C}$	60	mJ
$E_{AS}$		2.5	mJ
$dv/dt$	$I_S \leq I_{DM}$ , $di/dt \leq 100$ A/μs, $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ\text{C}$ , $R_G = 2$ Ω	15	V/ns
$P_D$	$T_C = 25^\circ\text{C}$	500	W
$T_J$		-55 to +150	°C
$T_{JM}$		150	°C
$T_{stg}$		-55 to +150	°C
$V_{ISOL}$	50/60 Hz, RMS $t = 1$ min	2500	V~
	$I_{ISOL} \leq 1$ mA $t = 1$ s	3000	V~
$M_d$	Mounting torque	1.5/13	Nm/lb.in.
	Terminal connection torque	1.5/13	Nm/lb.in.
<b>Weight</b>		30	g

miniBLOC, SOT-227 B (IXFN)  
E153432



G = Gate  
S = Source

Either Source terminal at miniBLOC can be used as Main or Kelvin Source

### Features

- IXYS advanced low  $Q_g$  process
- Low gate charge and capacitances
  - easier to drive
  - faster switching
- Unclamped Inductive Switching (UIS) rated
- Low  $R_{DS(on)}$
- Fast intrinsic diode
- International standard package
- miniBLOC with Aluminium nitride isolation for low thermal resistance
- Low terminal inductance (<10 nH) and stray capacitance to heatsink (<35pf)
- Molding epoxies meet UL 94 V-0 flammability classification

### Applications

- DC-DC converters
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- Temperature and lighting controls

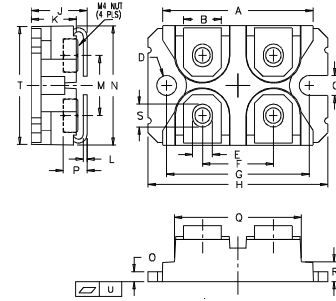
### Advantages

- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$V_{DSS}$	$V_{GS} = 0$ V, $I_D = 1$ mA	500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 4$ mA	2.0		V
$I_{GSS}$	$V_{GS} = \pm 20$ V <sub>DC</sub> , $V_{DS} = 0$			±100 nA
$I_{DSS}$	$V_{DS} = V_{DSS}$ $V_{GS} = 0$ V	$T_J = 25^\circ\text{C}$		100 μA
		$T_J = 125^\circ\text{C}$		2 mA
$R_{DS(on)}$	$V_{GS} = 10$ V, $I_D = 0.5$ $I_{D25}$	44N50		120 Ω
		48N50		100 Ω
Pulse test, $t \leq 300$ μs, duty cycle $d \leq 2$ %				

Symbol	Test Conditions	Characteristic Values		
		(T <sub>J</sub> = 25°C, unless otherwise specified)		
		min.	typ.	max.
<b>g<sub>fs</sub></b>	V <sub>DS</sub> = 20 V; I <sub>D</sub> = 0.5 • I <sub>D25</sub> , pulse test	30	42	S
<b>C<sub>iss</sub></b>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 25 V, f = 1 MHz		7000	pF
<b>C<sub>oss</sub></b>			960	pF
<b>C<sub>rss</sub></b>			230	pF
<b>t<sub>d(on)</sub></b>	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 0.5 • V <sub>DSS</sub> , I <sub>D</sub> = 0.5 • I <sub>D25</sub> R <sub>G</sub> = 4.7 Ω (External),		33	ns
<b>t<sub>r</sub></b>			22	ns
<b>t<sub>d(off)</sub></b>			75	ns
<b>t<sub>f</sub></b>			10	ns
<b>Q<sub>g(on)</sub></b>	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 0.5 • V <sub>DSS</sub> , I <sub>D</sub> = 0.5 • I <sub>D25</sub>		190	nC
<b>Q<sub>gs</sub></b>			40	nC
<b>Q<sub>gd</sub></b>			86	nC
<b>R<sub>thJC</sub></b>			0.26	K/W
<b>R<sub>thCK</sub></b>			0.05	K/W

Symbol	Test Conditions	Characteristic Values		
		(T <sub>J</sub> = 25°C, unless otherwise specified)		
		min.	typ.	max.
<b>I<sub>S</sub></b>	V <sub>GS</sub> = 0 V			48 A
<b>I<sub>SM</sub></b>	Repetitive; pulse width limited by T <sub>JM</sub>			192 A
<b>V<sub>SD</sub></b>	I <sub>F</sub> = I <sub>S</sub> , V <sub>GS</sub> = 0 V, Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %			1.5 V
<b>t<sub>rr</sub></b>	I <sub>F</sub> = 25A, -di/dt = 100 A/μs, V <sub>R</sub> = 100 V		1.0	250 ns
<b>Q<sub>RM</sub></b>			10	μC
<b>I<sub>RM</sub></b>				

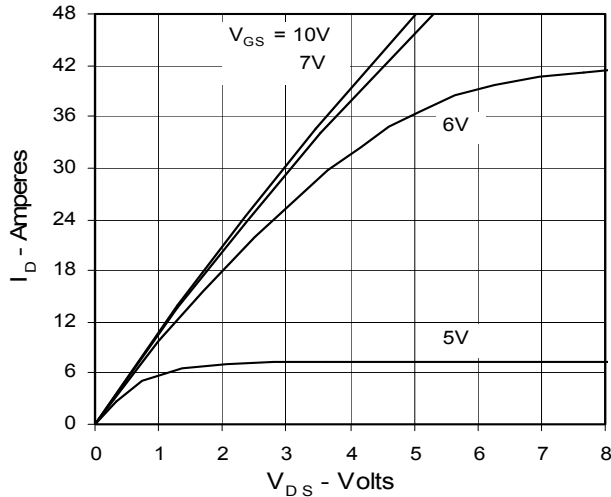
**miniBLOC, SOT-227 B**


M4 screws (4x) supplied

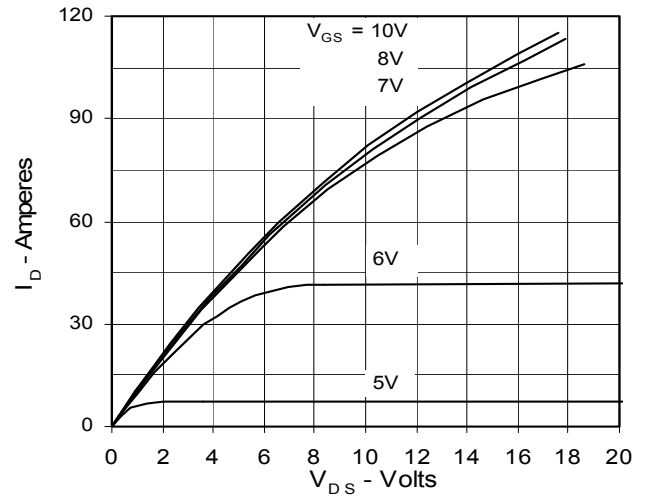
Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	38.00	38.23	1.496	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.76	0.84	0.030	0.033
M	12.60	12.85	0.496	0.506
N	25.15	25.42	0.990	1.001
O	1.98	2.13	0.078	0.084
P	4.95	5.97	0.195	0.235
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.174
S	4.72	4.85	0.186	0.191
T	24.59	25.07	0.968	0.987
U	-0.05	0.1	-0.002	0.004

IXYS reserves the right to change limits, test conditions, and dimensions.

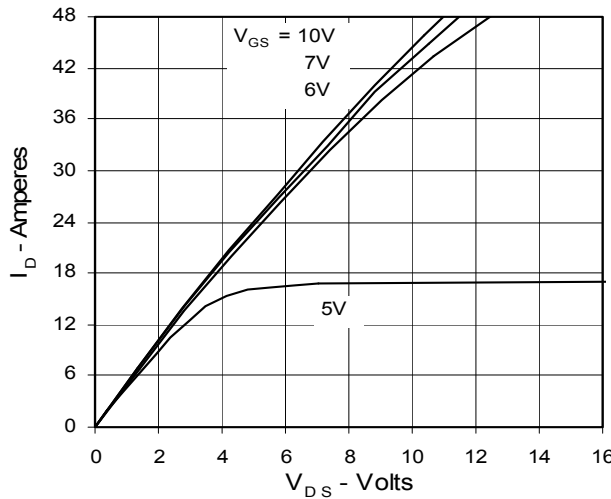
**Fig. 1. Output Characteristics  
@ 25 Deg. C**



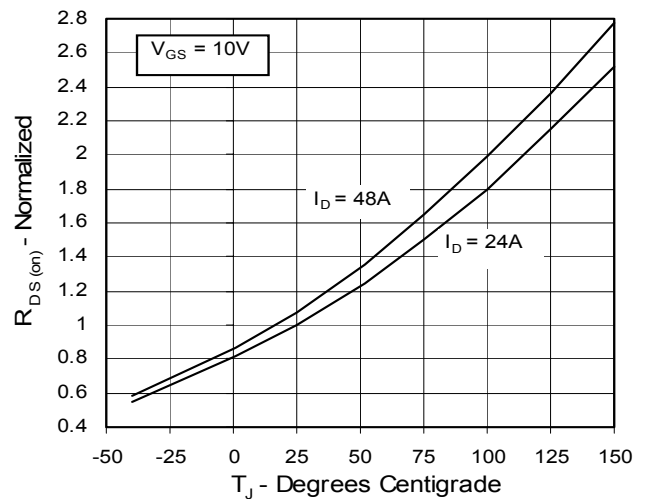
**Fig. 2. Extended Output Characteristics  
@ 25 deg. C**



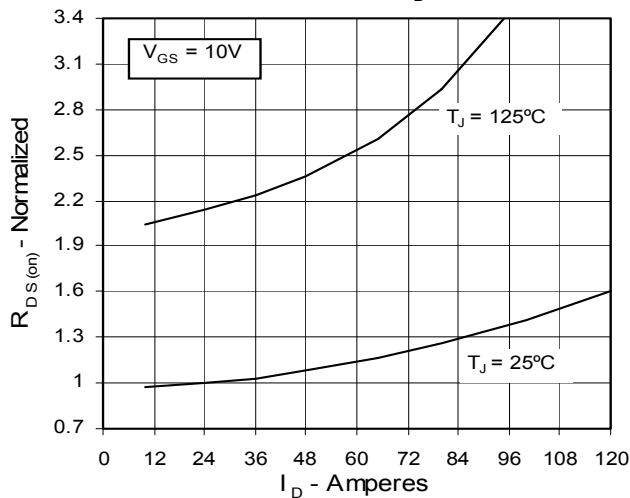
**Fig. 3. Output Characteristics  
@ 125 Deg. C**



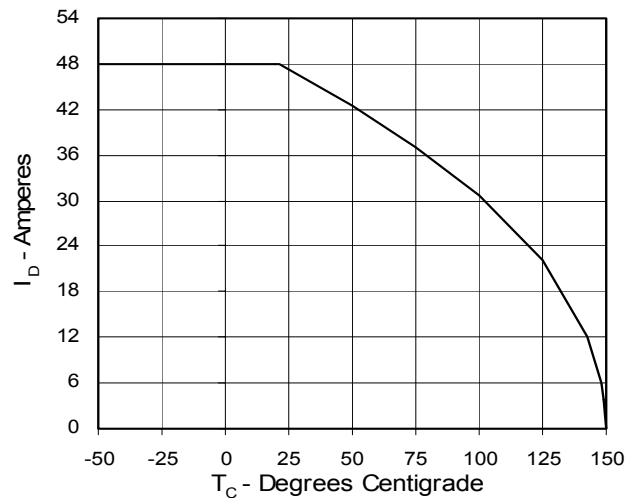
**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_{D25}$  Value vs.  
Junction Temperature**



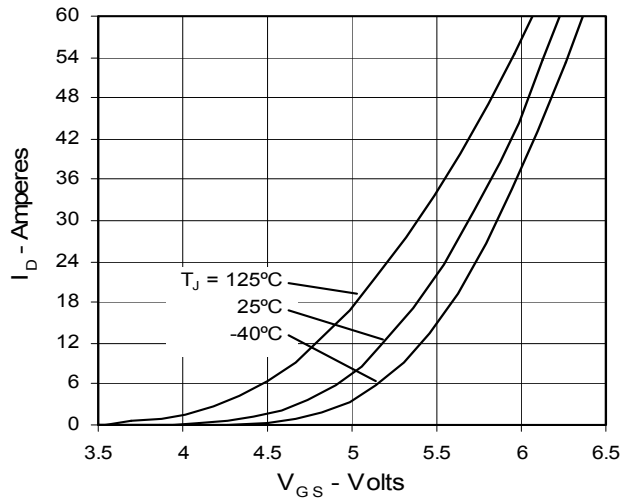
**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_{D25}$   
Value vs.  $I_D$**



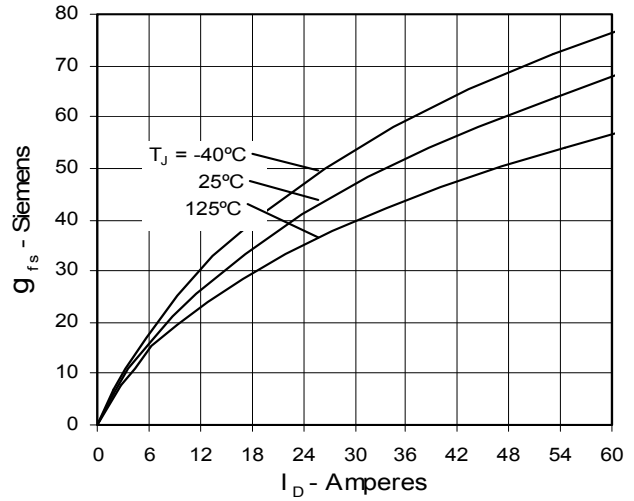
**Fig. 6. Drain Current vs. Case  
Temperature**



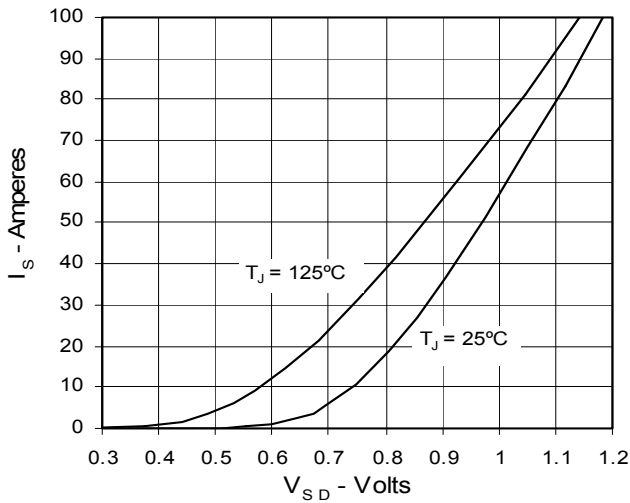
**Fig. 7. Input Admittance**



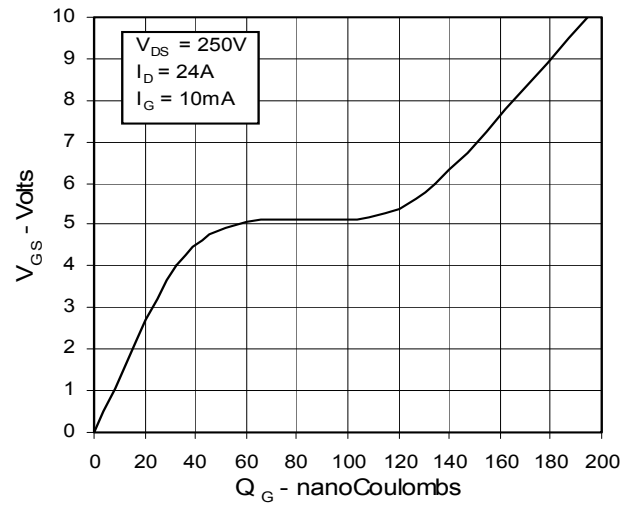
**Fig. 8. Transconductance**



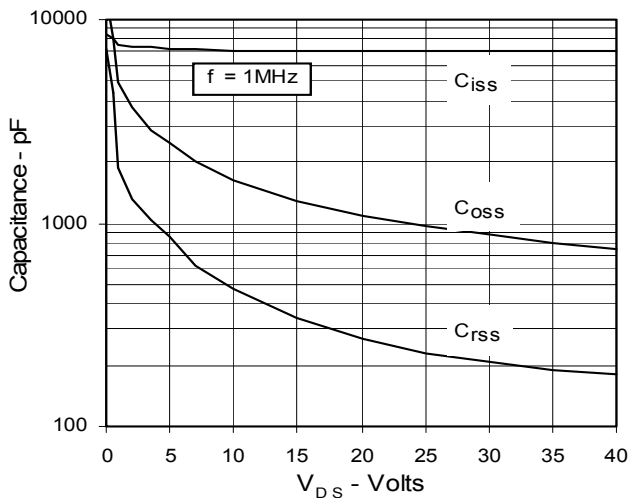
**Fig. 9. Source Current vs. Source-To-Drain Voltage**



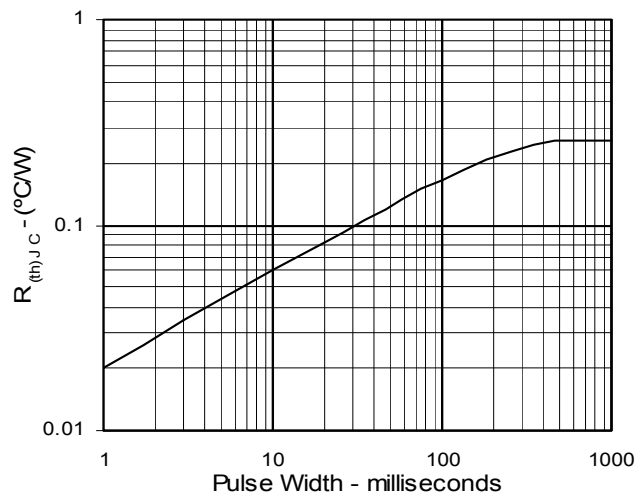
**Fig. 10. Gate Charge**



**Fig. 11. Capacitance**



**Fig. 12. Maximum Transient Thermal Resistance**



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